

CNA1011K (ON1113)

Photo Interrupter

For contactless SW and object detection

■ Overview

CNA1011K is a small size photocoupler package consisting of a high efficiency GaAs infrared light emitting diode used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element.

■ Features

- Highly precise position detection: 0.3 mm
- Wide gap between emitting and detecting elements, suitable for thick plate detection
- Fast response: t_r , t_f = 6.0 μ s (typ.)
- Small output current variation against change in temperature

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Input (Light emitting diode)	Power dissipation *1	P_D	75	mW
	Forward current	I_F	50	mA
	Reverse voltage	V_R	3	V
Output (Photo transistor)	Collector-emitter voltage (Base open)	V_{CEO}	30	V
	Emitter-collector voltage (Base open)	V_{ECO}	5	V
	Collector current	I_C	20	mA
	Collector power dissipation *2	P_C	100	mW
Operating ambient temperature		T_{opr}	-25 to +85	$^\circ\text{C}$
Storage temperature		T_{stg}	-30 to +100	$^\circ\text{C}$

Note) *1: Input power derating ratio is 1.0 mW/ $^\circ\text{C}$ at $T_a \geq 25^\circ\text{C}$

*2: Output power derating ratio is 1.34 mW/ $^\circ\text{C}$ at $T_a \geq 25^\circ\text{C}$

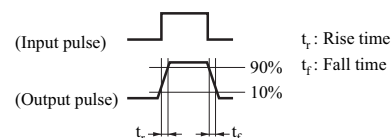
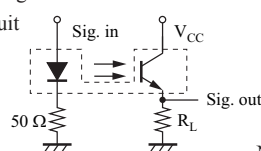
■ Electrical-Optical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Input characteristics	Reverse current	I_R	$V_R = 3\text{ V}$			10	μA
	Forward voltage	V_F	$I_F = 50\text{ mA}$		1.2	1.5	V
	Terminal capacitance	C_t	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$		35		pF
Output characteristics	Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 10\text{ V}$			200	nA
	Collector-emitter capacitance	C_C	$V_{CE} = 10\text{ V}$, $f = 1\text{ MHz}$		5		pF
Transfer characteristics	Collector current	I_C	$V_{CC} = 10\text{ V}$, $I_F = 20\text{ mA}$, $R_L = 100\ \Omega$	0.3			mA
	Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_F = 50\text{ mA}$, $I_C = 0.1\text{ mA}$			0.5	V
	Rise time *	t_r	$V_{CC} = 10\text{ V}$, $I_C = 1\text{ mA}$, $R_L = 100\ \Omega$		6.0		μs
	Fall time *	t_f			6.0		μs

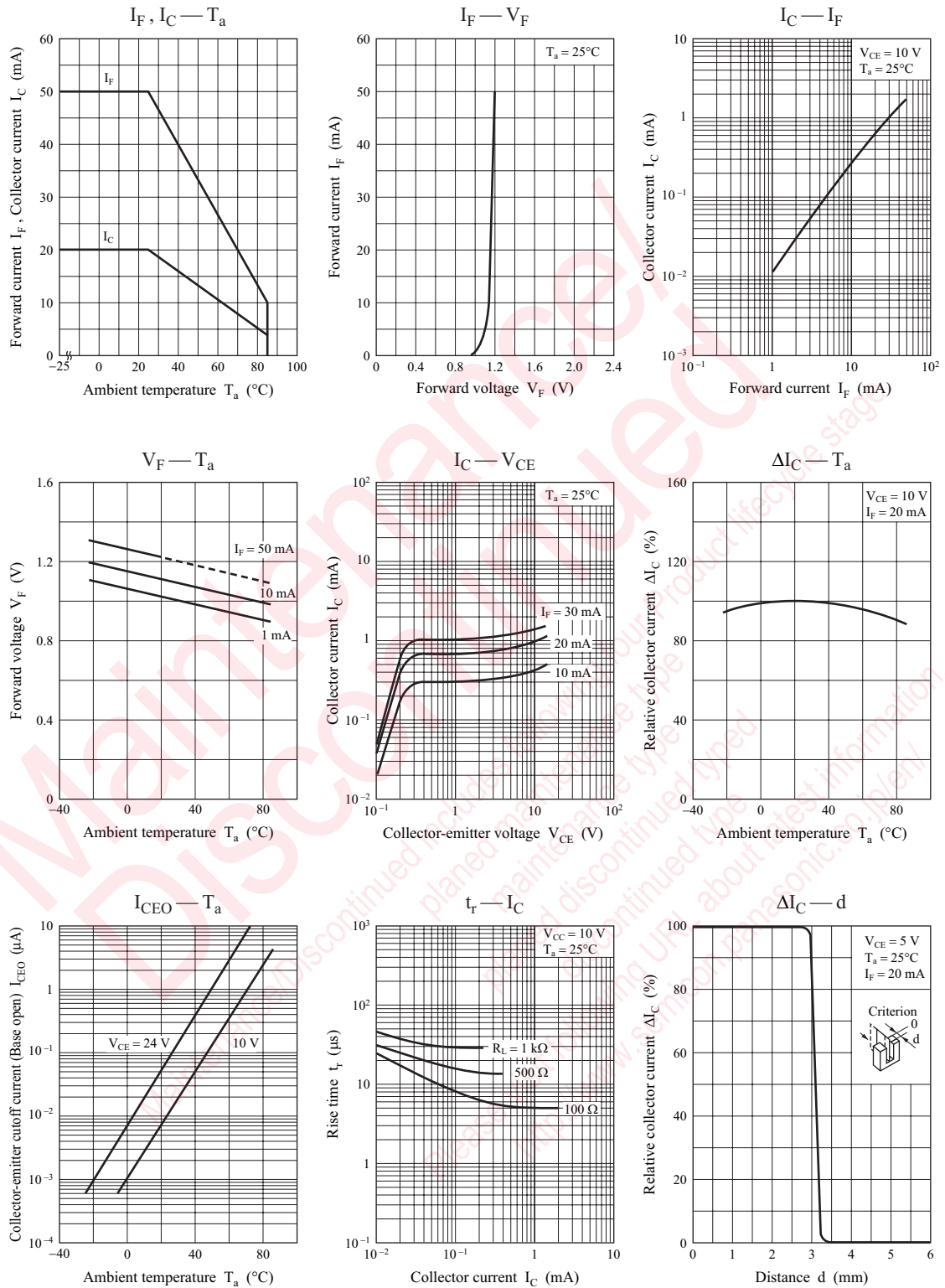
Note) 1. Input and output are practiced by electricity.

2. This device is designed by disregarding radiation.

3. *: Switching time measurement circuit

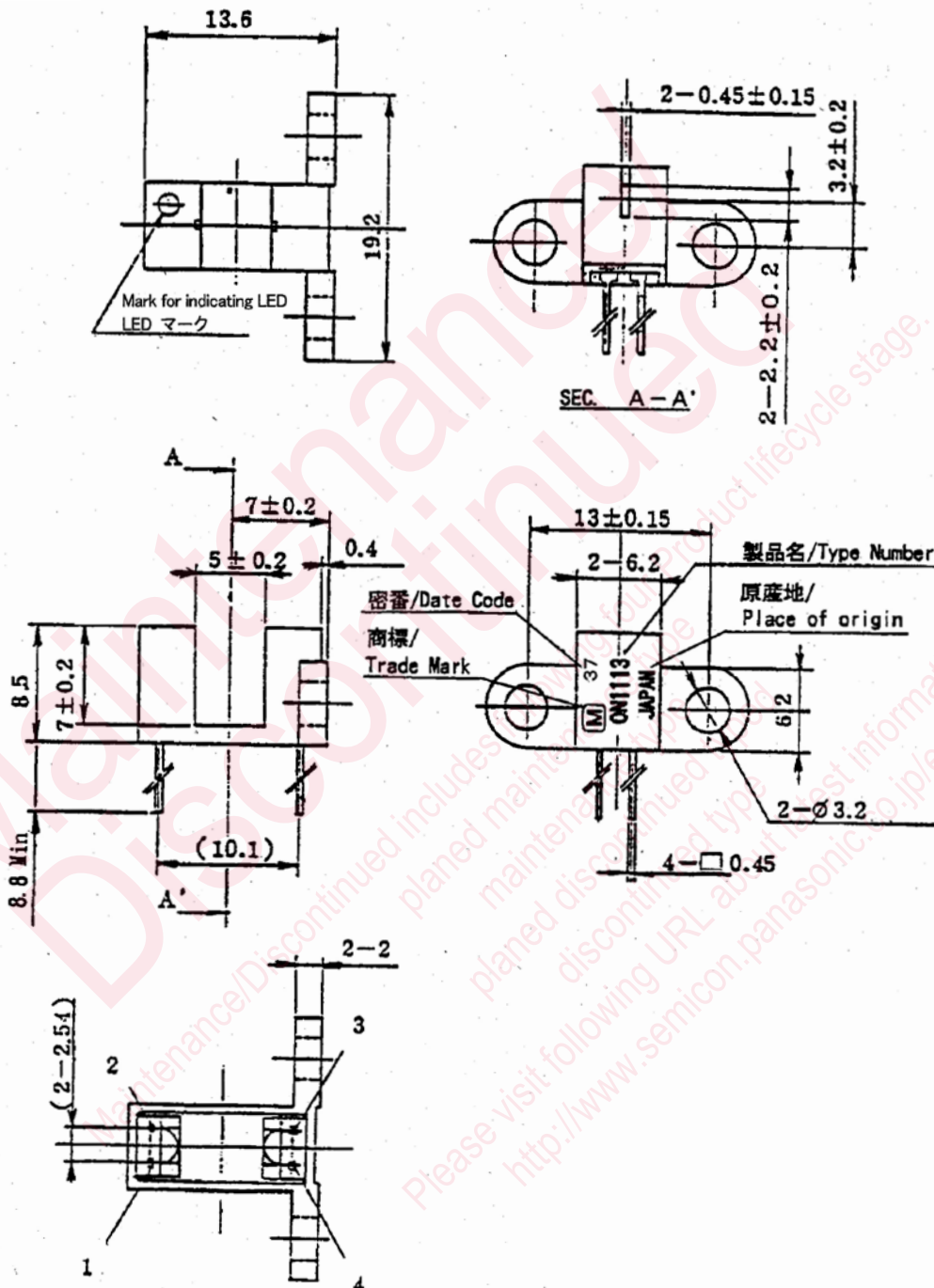


Note) The part number in the parenthesis shows conventional part number.



■ Package (Unit: mm)

LSSSIR4S0004



(注 1) 指示なき寸法公差: ± 0.3 / (Note 1) No appointment tolerance: ± 0.3

(注 2) マークは、目視又は顕微鏡に於いて解読できる事。

(Note 2) What a mark sees an attention and can decode in a microscope.

• Pin name

- 1: Anode
- 2: Cathode
- 3: Collector
- 4: Emitter

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